



## EMIF02-MIC03C2

### 2 line EMI filter and ESD protection

#### Main product characteristics

Where EMI filtering in ESD sensitive equipment is required:

- Mobile phones and communication systems
- Computers and printers and MCU Boards

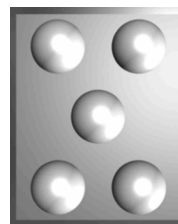
#### Description

The EMIF02-MIC03C2 is a highly integrated device designed to suppress EMI/RFI noise in all systems subjected to electromagnetic interference. The Flip-Chip packaging means the package size is equal to the die size.

This filter includes ESD protection circuitry, which prevents damage to the application when it is subjected to ESD surges up to 15 kV.

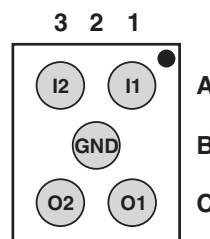
#### Benefits

- EMI symmetrical (I/O) low-pass filter
- High efficiency EMI filter (-35 dB @ 900 MHz)
- Very low PCB space consumption:  
1.07 mm x 1.47 mm
- Very thin package: 0.695 mm
- Coating resin on back side and lead free package
- High efficiency in ESD suppression
- High reliability offered by monolithic integration
- High reduction of parasitic elements through integration and wafer level packaging.



**Coated Flip-Chip package  
(about 20 times real size)**

#### Pin configuration (Bump side)



#### Complies with following standards:

IEC 61000-4-2

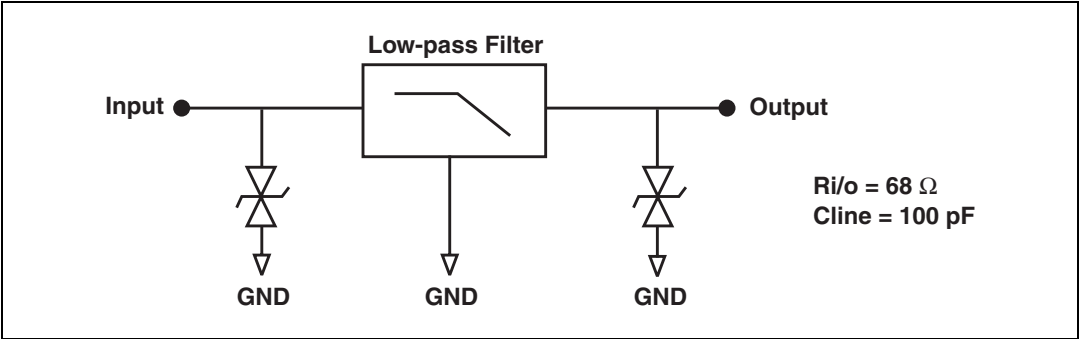
|                    |       |                     |
|--------------------|-------|---------------------|
| level 4 input pins | 15 kV | (air discharge)     |
|                    | 8 kV  | (contact discharge) |

|                     |      |                     |
|---------------------|------|---------------------|
| level 1 output pins | 2 kV | (air discharge)     |
|                     | 2 kV | (contact discharge) |

MIL STD 883G - Method 3015-7 Class 3

# 1 Characteristics

**Figure 1. Basic cell configuration**



**Table 1. Absolute ratings (limiting values)**

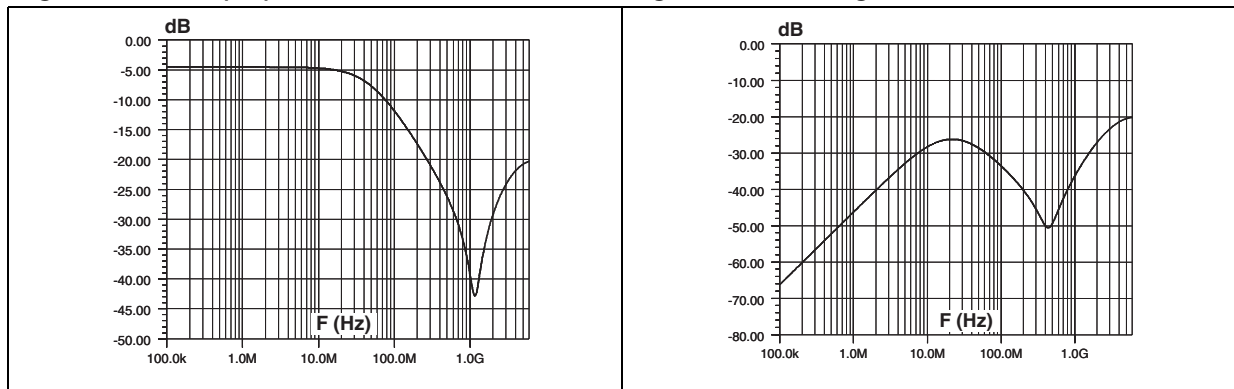
| Symbol    | Parameter                    | Value       | Unit |
|-----------|------------------------------|-------------|------|
| $T_j$     | Maximum junction temperature | 125         | °C   |
| $T_{op}$  | Operating temperature range  | -40 to +85  | °C   |
| $T_{stg}$ | Storage temperature range    | -55 to +150 | °C   |

**Table 2. Electrical characteristics ( $T_{amb} = 25^\circ \text{C}$ )**

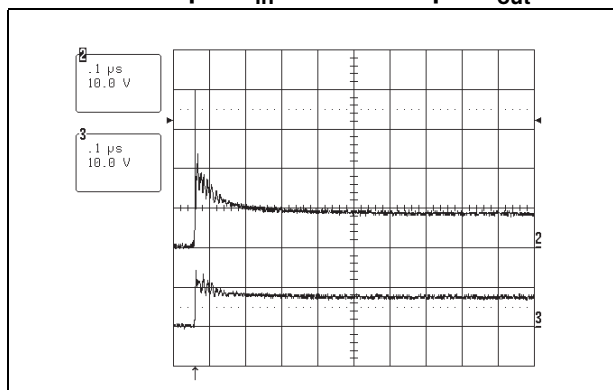
| Symbol     | Parameters                                 |  |
|------------|--|--|
| $V_{BR}$   | Breakdown voltage                          |  |
| $I_{RM}$   | Leakage current @ $V_{RM}$                 |  |
| $V_{RM}$   | Stand-off voltage                          |  |
| $V_{CL}$   | Clamping voltage                           |  |
| $R_d$      | Dynamic impedance                          |  |
| $I_{PP}$   | Peak pulse current                         |  |
| $R_{I/O}$  | Series resistance between input and output |  |
| $C_{line}$ | Input capacitance per line                 |  |

| Symbol     | Test conditions                 | Min | Typ | Max | Unit     |
|------------|---------------------------------|-----|-----|-----|----------|
| $V_{BR}$   | $I_R = 1 \text{ mA}$            | 6   | 8   |     | V        |
| $I_{RM}$   | $V_{RM} = 3 \text{ V per line}$ |     |     | 500 | nA       |
| $R_{I/O}$  | Tolerance                       |     | 68  |     | $\Omega$ |
| $C_{line}$ | $V_R = 0 \text{ V}$             |     | 100 |     | pF       |

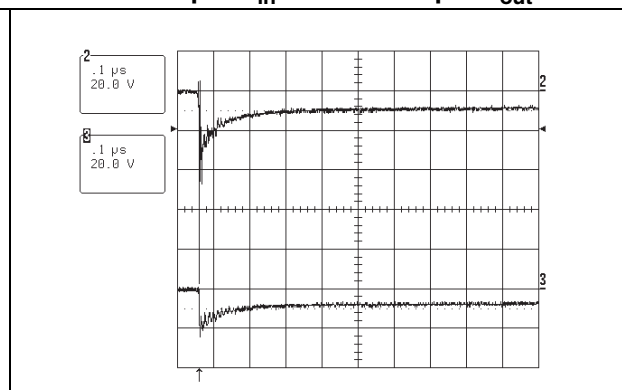
**Figure 2. S21 (dB) attenuation measurement** **Figure 3. Analog crosstalk measurement**



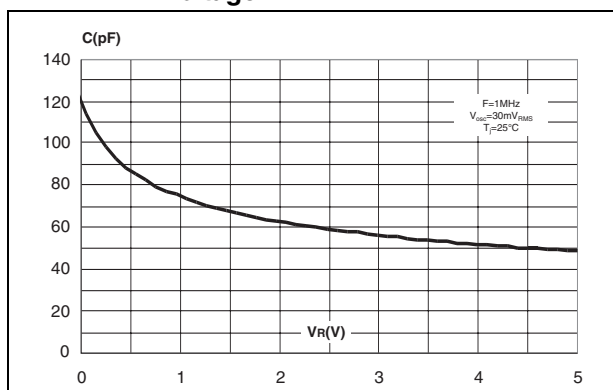
**Figure 4. ESD response to IEC 61000-4-2 (+15 kV air discharge) on one input  $V_{in}$  and one output  $V_{out}$**



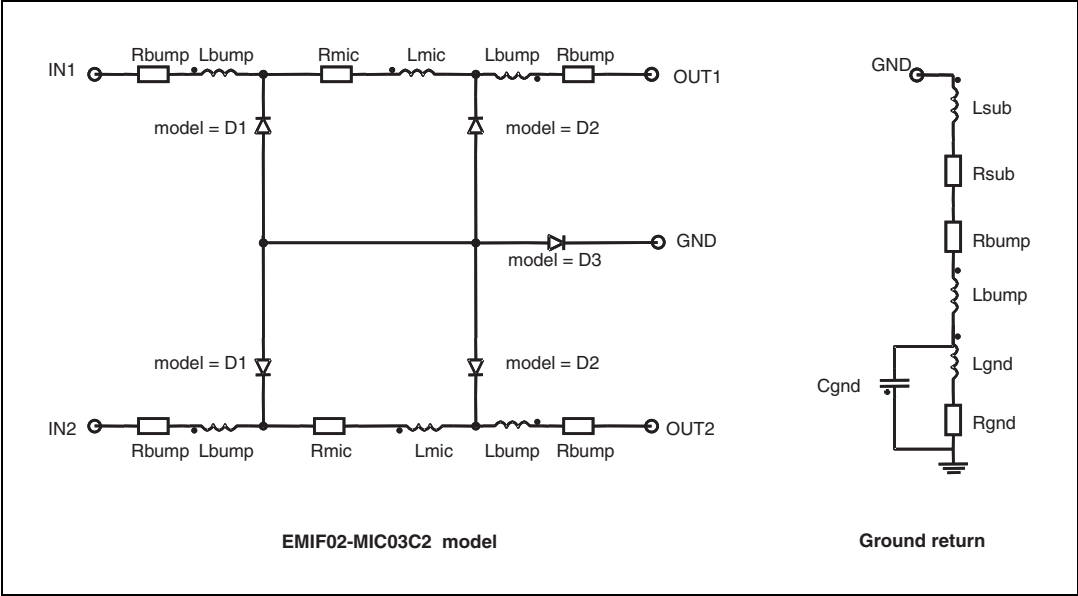
**Figure 5. ESD response to IEC 61000-4-2 (-15 kV air discharge) on one input  $V_{in}$  and one output  $V_{out}$**



**Figure 6. Line capacitance versus applied voltage**



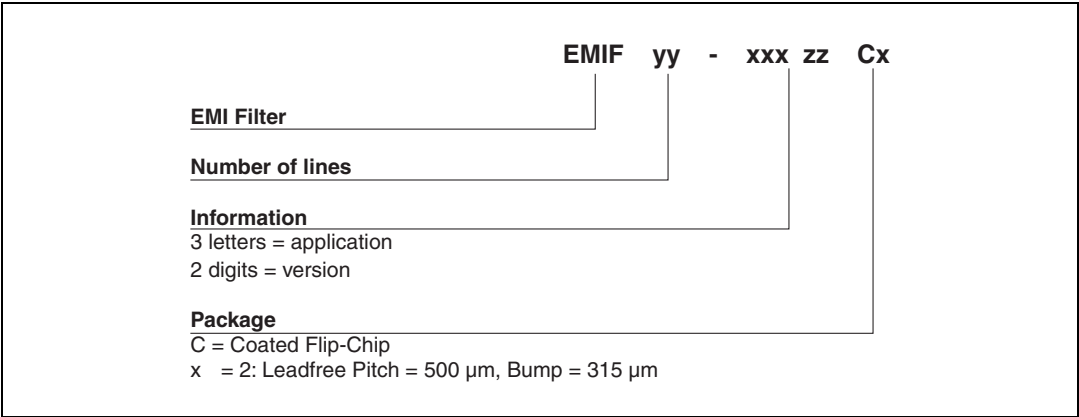
**Figure 7. Aplac model**



**Figure 8. Aplac parameters**

|             |             |             |                         |
|-------------|-------------|-------------|-------------------------|
| Model D1    | Model D3    | Model D2    | aplacvar Rmic 68        |
| CJO=Cdiode1 | CJO=Cdiode3 | CJO=Cdiode2 | aplacvar Lmic 10p       |
| BV=7        | BV=7        | BV=7        | aplacvar Cdiode1 100pF  |
| IBV=1u      | IBV=1u      | IBV=1u      | aplacvar Cdiode2 3.6pF  |
| IKF=1000    | IKF=1000    | IKF=1000    | aplacvar Cdiode3 1.17nF |
| IS=10f      | IS=10f      | IS=10f      | aplacvar Lbump 50pH     |
| ISR=100p    | ISR=100p    | ISR=100p    | aplacvar Rbump 20m      |
| N=1         | N=1         | N=1         | aplacvar Rsub 0.5m      |
| M=0.3333    | M=0.3333    | M=0.3333    | aplacvar Rgnd 10m       |
| RS=0.7      | RS=0.12     | RS=0.3      | aplacvar Lgnd 50pH      |
| VJ=0.6      | VJ=0.6      | VJ=0.6      | aplacvar Cgnd 0.15pF    |
| TT=50n      | TT=50n      | TT=50n      | aplacvar Lsub 10pH      |

2 Ordering information scheme



3 Package information

Figure 9. Flip-Chip Dimensions

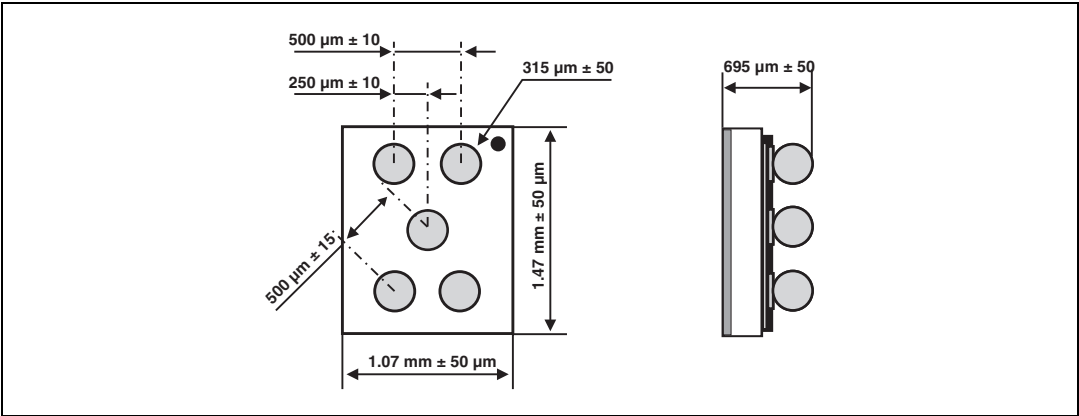


Figure 10. Marking

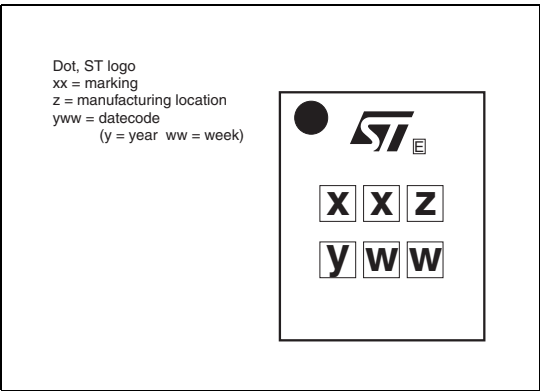
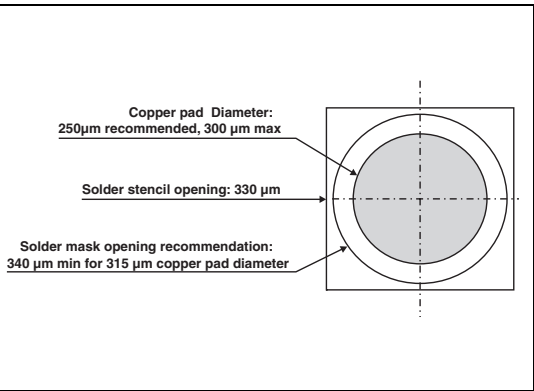


Figure 11. Footprint recommendation



Dot identifying Pin A1 location

$4 \pm 0.1$

$\text{Ø } 1.5 \pm 0.1$

$1.75 \pm 0.1$

$3.5 \pm 0.1$

$8 \pm 0.3$

$0.73 \pm 0.05$

$4 \pm 0.1$

User direction of unreeling

ST  
xxz  
yww

ST  
xxz  
yww

ST  
xxz  
yww

All dimensions in mm

## 4 Ordering information

| Ordering code  | Marking | Package   | Weight | Base qty | Delivery mode    |
|----------------|---------|-----------|--------|----------|------------------|
| EMIF02-MIC03C2 | FW      | Flip-Chip | 2.3 mg | 5000     | 7" Tape and reel |

## 5 Revision history

| Date        | Revision | Changes          |
|-------------|----------|------------------|
| 28-Nov-2006 | 1        | Initial release. |

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